



NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE1540AD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

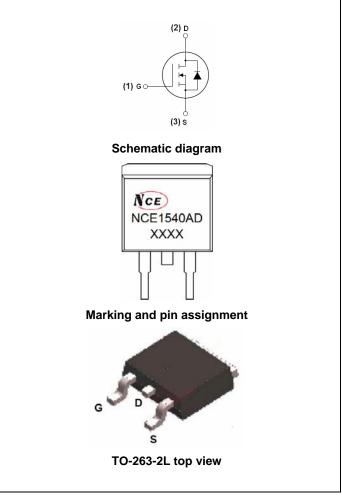
- $V_{DS} = 150V, I_D = 40A$ $R_{DS(ON)} < 45m\Omega @ V_{GS} = 10V$ (Typ:35m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1540AD	NCE1540AD	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	150	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	Ι _D	40	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	29	А
Pulsed Drain Current	I _{DM}	164	А
Maximum Power Dissipation	PD	140	W
Derating factor		0.93	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	310	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.07	°C/W
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Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·	·				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	150	170	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·	·				
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	0.8	1.05	1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =18A	-	35	45	mΩ
Forward Transconductance	g fs	V _{DS} =15V,I _D =18A	38	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}		-	4200	-	PF
Output Capacitance	C _{oss}	$V_{DS}=25V, V_{GS}=0V,$	-	203	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	96	-	PF
Switching Characteristics (Note 4)			1			
Turn-on Delay Time	t _{d(on)}		-	17.8	_	nS
Turn-on Rise Time	tr	V_{DD} =30V,I _D =2A,R _L =15 Ω	-	11.8	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =10V,R _G =2.5Ω	-	56	-	nS
Turn-Off Fall Time	t _f	-	-	14.6	-	nS
Total Gate Charge	Qg	N/ 201/1 201		105	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V,I _D =30A,		21	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V		31.5	-	nC
Drain-Source Diode Characteristics			1			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =18A	-	0.8	1.2	V
Diode Forward Current (Note 2)	Is		-	-	40	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 18A	-	70	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	230	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				y LS+LD)

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^\circ\!\mathrm{C}$, V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

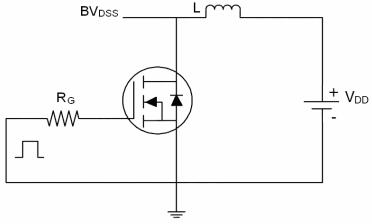


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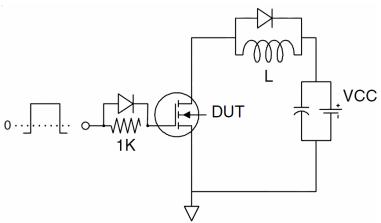
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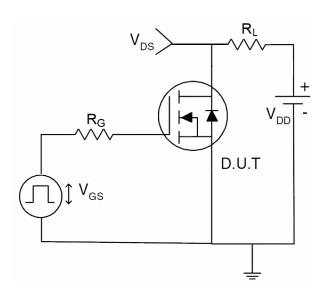
Test Circuit 1) E_{AS} test Circuit



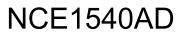
2) Gate charge test Circuit



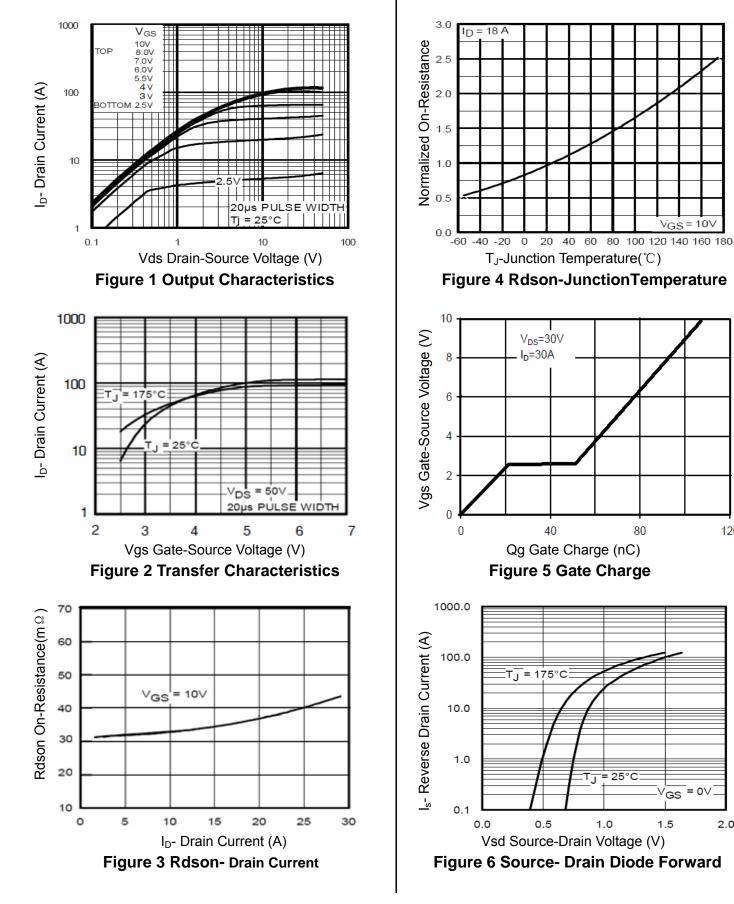
3) Switch Time Test Circuit







Typical Electrical and Thermal Characteristics (Curves)

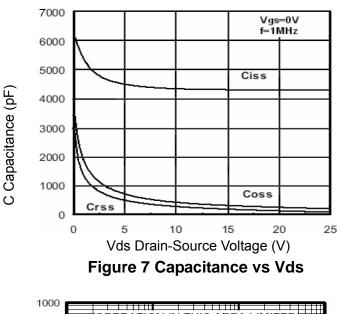


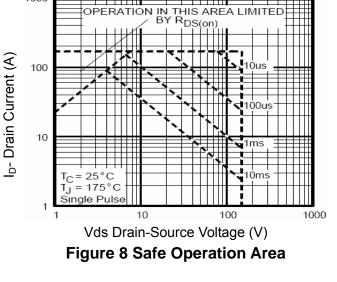
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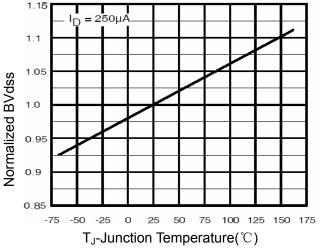
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NCE1540AD

Figure 9 BV_{DSS} vs Junction Temperature

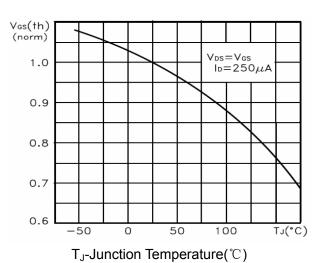
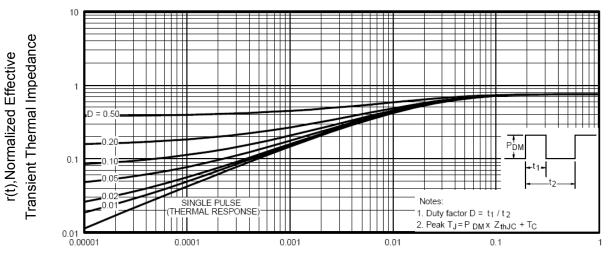


Figure 10 V_{GS(th)} vs Junction Temperature

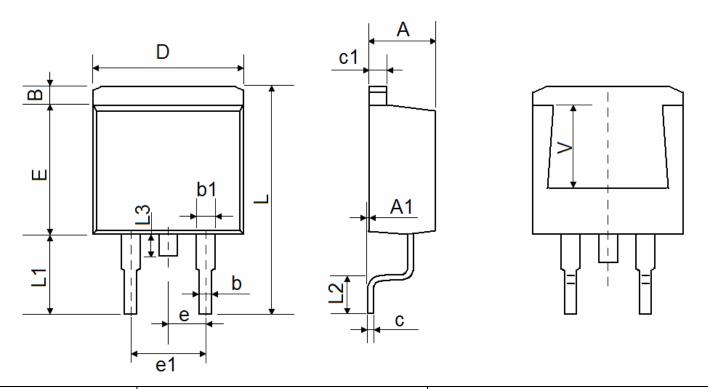


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance





TO-263-2L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	2.540 TYP.		ΓΥΡ.	
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.600	REF	0.220 REF		







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